



## R-C Thermal Model Parameters

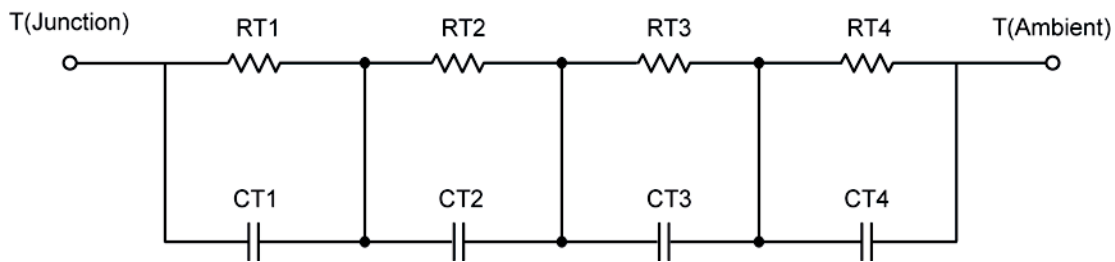
### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*  
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	10.7568	N/A	3.0651
RT2	38.6781	N/A	43.8693
RT3	34.7951	N/A	11.3230
RT4	40.7699	N/A	11.7426
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.3053 m	N/A	263.8942 u
CT2	38.5832 m	N/A	29.7486 m
CT3	24.6875 m	N/A	79.1707 m
CT4	1.6892	N/A	4.8454 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	13.9187	N/A	4.2361
RF2	40.4017	N/A	18.1356
RF3	31.8717	N/A	19.8866
RF4	38.8080	N/A	27.7418
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.3348 m	N/A	283.8979 $\mu$
CF2	13.2984 m	N/A	4.4710 m
CF3	10.7206 m	N/A	18.4202 m
CF4	1.8651	N/A	6.8324 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

